WHAT IS CLAIMED IS:

- 1 1. A fabricating method for an array substrate of a liquid crystal display device, the
- 2 method comprising:
- forming a gate line including a gate electrode on a substrate;
- forming a gate-insulating layer on the substrate, the gate-insulating layer covering the
- 5 gate line and gate electrode;
- forming an active layer on the gate-insulating layer;
 - forming a data line, a source electrode and a drain electrode on the active layer;
 - forming a passivation layer on the gate-insulating layer, the passivation layer covering
 - the data line, source electrode and drain electrode;
 - dry-etching a surface of the passivation layer with a gas such that the surface is
 - embossed; and

1202

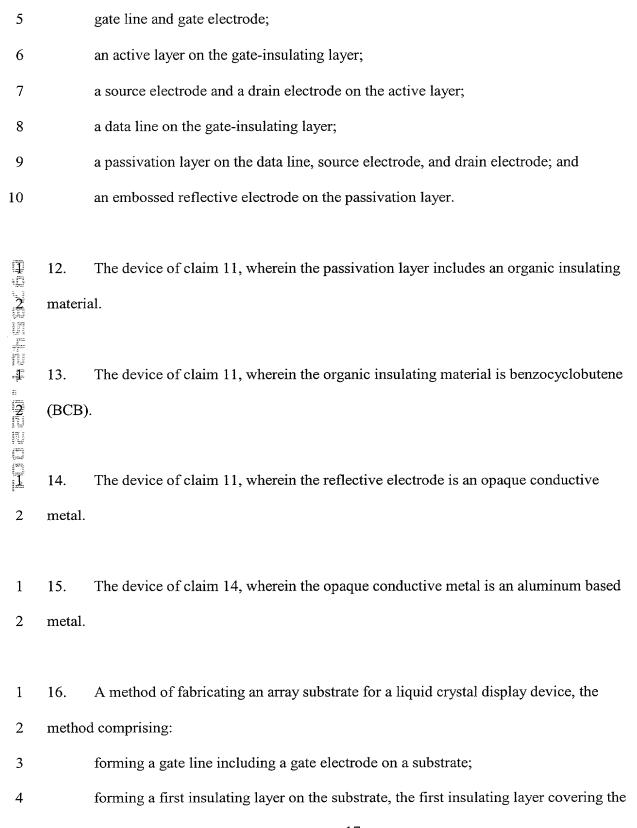
13

- forming a reflective electrode on the embossed surface of the passivation layer such
- that an exterior surface of the reflective electrode is embossed.
- 1 2. The method of claim 1, wherein the gas used for the dry-etching is a mixture gas of
- 2 $SF_6 + O_2$.
- 1 3. The method of claim 1, wherein the gas used for the dry-etching is a mixture gas of
- 2 $CF_4 + O_2$.
- 1 4. The method of claim 1, wherein the gas used for the dry-etching is O₂ gas.

DC:71512.2

5. The method of claim 1, wherein the passivation layer includes an organic insulating 1 2 material. The method of claim 5, wherein the organic insulating material is benzocyclobutene 6. 1 2 (BCB). The method of claim 1, wherein the reflective electrode is an opaque conductive 1 7. metal. The method of claim 7, wherein the opaque conductive metal is an aluminum based 8. metal. The method of claim 1, further including forming a contact hole in the passivation 9. layer prior to forming a reflective electrode on the embossed surface of the passivation layer such that an exterior surface of the reflective electrode is embossed. 3 The method of claim 1, further including forming a contact hole in the passivation 10. 1 layer prior to dry-etching the surface of the passivation layer. 2 A liquid crystal display device comprising: 1 11. upper and lower substrates with a liquid crystal layer interposed therebetween; 2 a gate line and a gate electrode on the lower substrate; 3 a gate-insulating layer on the lower substrate, the gate-insulating layer covering the 4

16



DC:71512.2

5	gate line and gate electrode;	
6	forming an active layer on the first insulating layer;	
7	forming a data line, a source electrode and a drain electrode on the active layer;	
8	forming a second insulating layer on the data line, source electrode and drain	
9	electrode;	
10	forming a first contact hole in the second insulating layer, exposing a first portion of	of
11	the drain electrode;	
12	forming a transparent electrode contacting the drain electrode via the first contact	
13 14 15	hole;	
14	forming a passivation layer on the first insulating layer and transparent electrode;	
	forming a second contact hole in the passivation layer and the second insulating lay	/er
16	exposing a second portion of the drain electrode;	
16	dry-etching a surface of the passivation layer with a gas such that the surface is	
18	embossed; and	
19	forming a reflective electrode on the embossed surface of the passivation layer such	h
20	that an exterior surface of the reflective electrode is embossed.	
1	17. The method of claim 16, wherein the gas used for the dry-etching is a mixture gas	of
2	$SF_6 + O_2$.	
1	18. The method of claim 16, wherein the gas used for the dry-etching is a mixture gas	of
2	$CF_4 + O_2$.	

18 DC:71512.2

The method of claim 16, wherein the gas used for the dry-etching is O₂ gas. 1 19. The method of claim 16, wherein the passivation layer includes an organic insulating 1 20. 2 material. The method of claim 20, wherein the organic insulating material is benzocyclobutene 1 21. 2 (BCB). The method of claim 16, wherein the reflective electrode is an opaque conductive 22. metal. The method of claim 22, wherein the opaque conductive metal is an aluminum based 23. metal. A liquid crystal display device comprising: 1 24. upper and lower substrates with a liquid crystal layer interposed therebetween; 2 3 a gate line and a gate electrode on the lower substrate; a first insulating layer on the lower substrate, the first insulating layer covering the 4 gate line and gate electrode; 5 an active layer on the gate-insulating layer; 6 a source electrode and a drain electrode on the active layer; 7 a data line on the gate-insulating layer; 8

a second insulating layer on the data line, source electrode and drain electrode;

DC:71512.2

9

10 a transparent electrode on the second insulating layer; 11 a passivation layer on the second insulating layer and the transparent electrode; and 12 an embossed reflective electrode on the passivation layer. 25. The device of claim 24, wherein the passivation layer includes an organic insulating 1 2 material. The device of claim 24, wherein the organic insulating material is benzocyclobutene 26. (BCB). 27. The device of claim 24, wherein the reflective electrode is an opaque conductive metal. 28. The device of claim 27, wherein the opaque conductive metal is an aluminum based

DC:71512.2 20

2

metal.